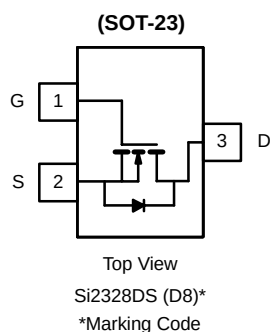


N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.300 @ $V_{GS} = 10$ V	1.5



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V _{DS}	100		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	1.5	1.15	A
Pulsed Drain Current ^b		I _{DM}	6		
Avalanche Current ^b	L = 0.1 mH	I _{AS}	6		
Single Avalanche Energy		E _{AS}	1.8		mJ
Continuous Source Current (Diode Conduction) ^a		I _S	0.6		A
Power Dissipation ^a	T _A = 25°C	P _D	1.25	0.73	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	80	100	$^\circ\text{C/W}$
	Steady State		130	170	
Maximum Junction-to-Foot	Steady State	R_{thJF}	45	55	

Notes

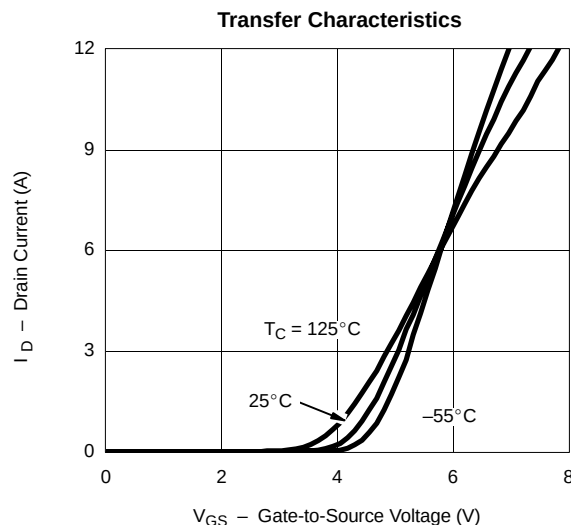
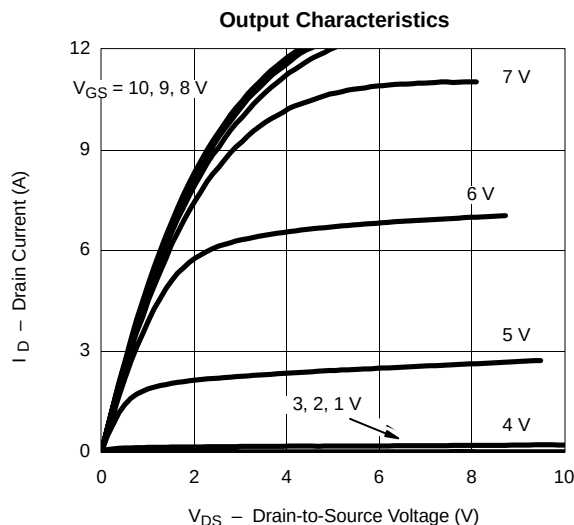
- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250uA	100			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.3		2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			200	nA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 15 V, V _{GS} = 10 V	6			A
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 1.5 A			0.300	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 1.5 A		4		S
Diode Forward Voltage	V _{SD}	I _S = 1.0 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 1.5 A		3.3	4.0	nC
Gate-Source Charge	Q _{gs}			0.47		
Gate-Drain Charge	Q _{gd}			1.45		
Switching						
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 33 Ω I _D ≅ 0.2 A, V _{GEN} = 10 V, R _G = 6 Ω		7	11	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			9	15	
Fall-Time	t _f			10	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.5 A, di/dt = 100 A/μs		50	100	ns

Notes

- a. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





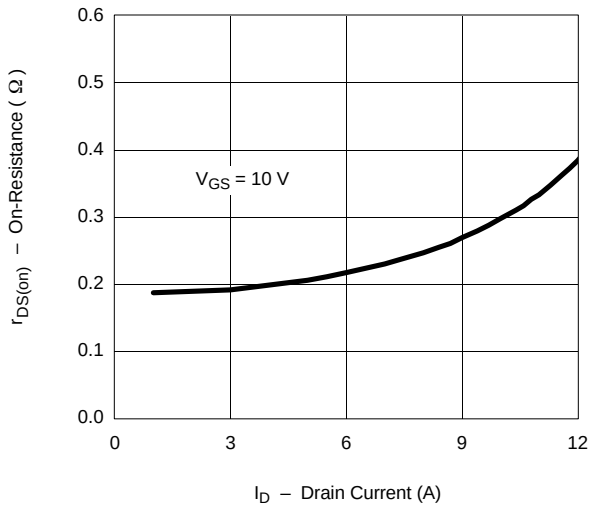
TUO FENG

Shenzhen Tuofeng Semiconductor Technology Co., Ltd

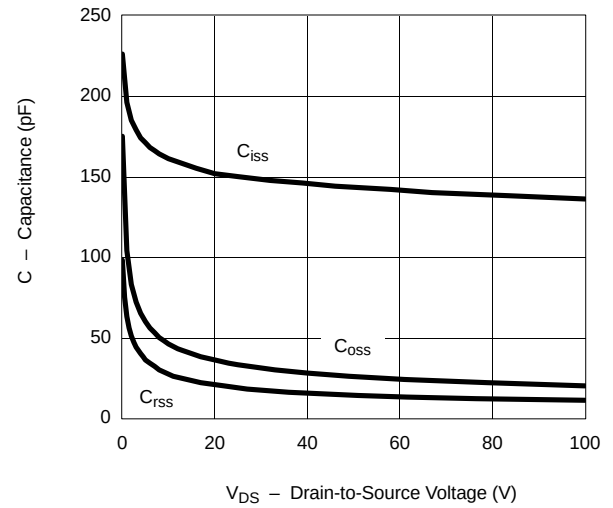
Si2328

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

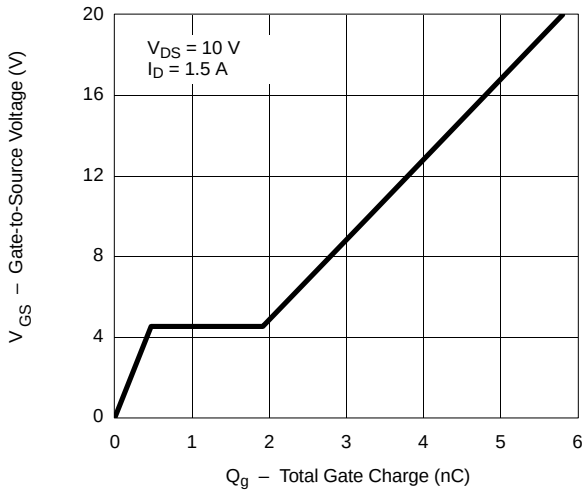
On-Resistance vs. Drain Current



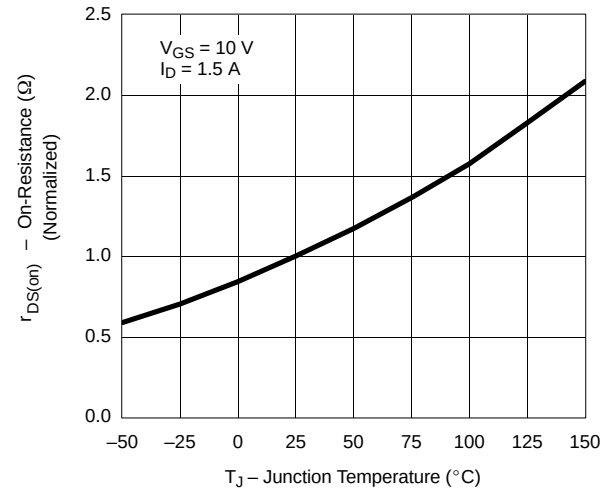
Capacitance



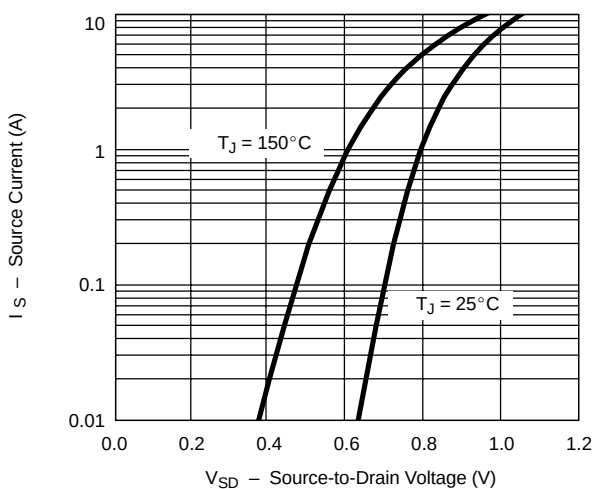
Gate Charge



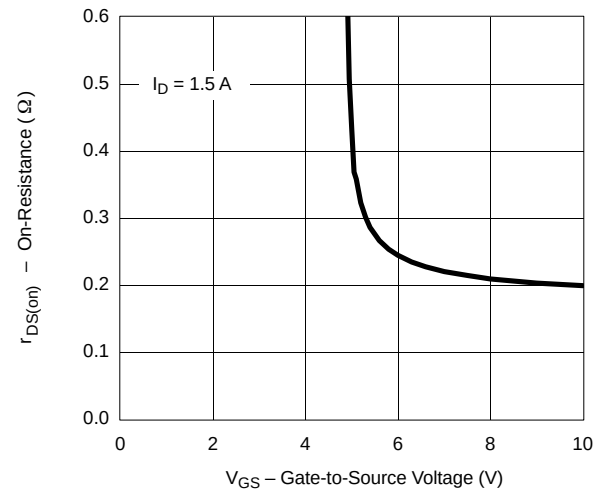
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

